



Description

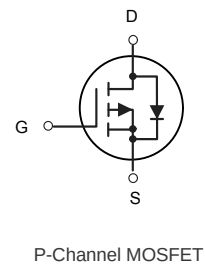
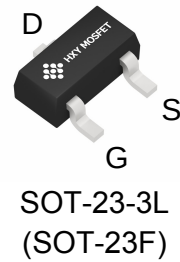
The SSM3J334R uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = -30V, I_D = -4.1A$
 $R_{DS(ON)} < 55m\Omega @ V_{GS}=10V$

Application

High power and current handing capability
Lead free product is acquired
Surface mount package
PWM applications
Load switch
Power management



Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
SSM3J334R	SOT-23-3L(SOT-23F)	HXY MOSFET	3000

Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-Continuous	-4.1	A
I_{DM}	Drain Current-Pulsed (Note 1)	-13	A
P_D	Maximum Power Dissipation	1.32	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}C$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 2)	125	$^{\circ}C/W$



Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=-1mA$	---	-0.02	---	V/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V$, $I_D=-3A$	---	42	55	m Ω
		$V_{GS}=-4.5V$, $I_D=-1.5A$	---	90	98	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu A$	-1.2	-1.5	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.32	---	mV/ $^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-24V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-24V$, $V_{GS}=0V$, $T_J=55^\circ\text{C}$	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-5V$, $I_D=-3A$	---	4.8	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1MHz$	---	24	48	Ω
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-20V$, $V_{GS}=-4.5V$, $I_D=-3A$	---	5.22	7.3	nC
Q_{gs}	Gate-Source Charge		---	1.25	1.8	
Q_{gd}	Gate-Drain Charge		---	2.3	3.2	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-15V$, $V_{GS}=-10V$, $R_G=3.3\Omega$ $I_D=-1A$	---	18.4	37	ns
T_r	Rise Time		---	11.4	21	
$T_{d(off)}$	Turn-Off Delay Time		---	39.4	79	
T_f	Fall Time		---	5.2	10.4	
C_{iss}	Input Capacitance	$V_{DS}=-15V$, $V_{GS}=0V$, $f=1MHz$	---	463	650	pF
C_{oss}	Output Capacitance		---	82	115	
C_{rss}	Reverse Transfer Capacitance		---	68	95	
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	-3.2	A
I_{SM}	Pulsed Source Current ^{2,4}		---	---	-13	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=-1A$, $T_J=25^\circ\text{C}$	---	---	-1	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

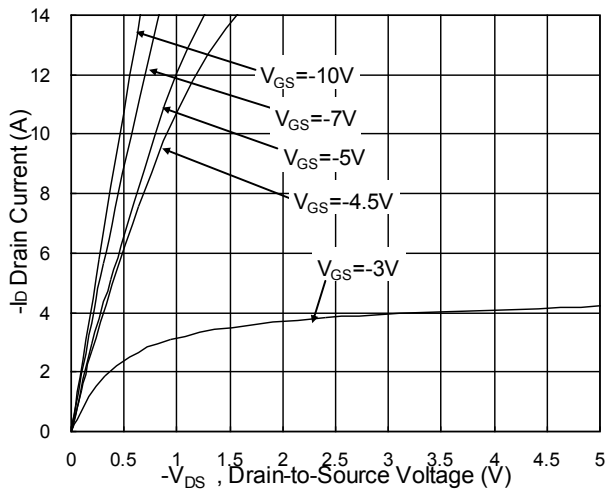


Fig.1 Typical Output Characteristics

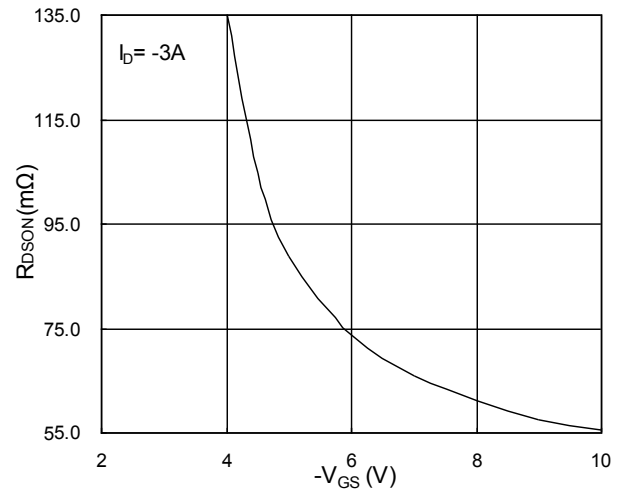


Fig.2 On-Resistance vs. G-S Voltage

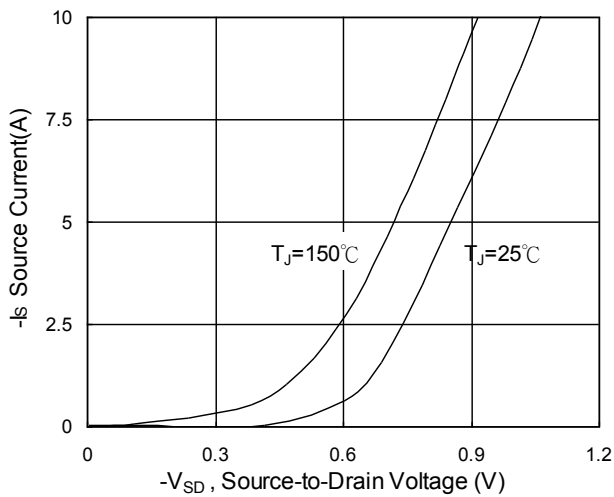


Fig.3 Source Drain Forward Characteristics

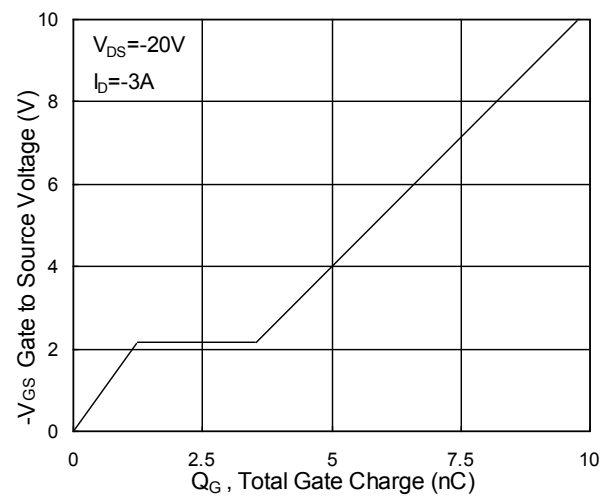


Fig.4 Gate-Charge Characteristics

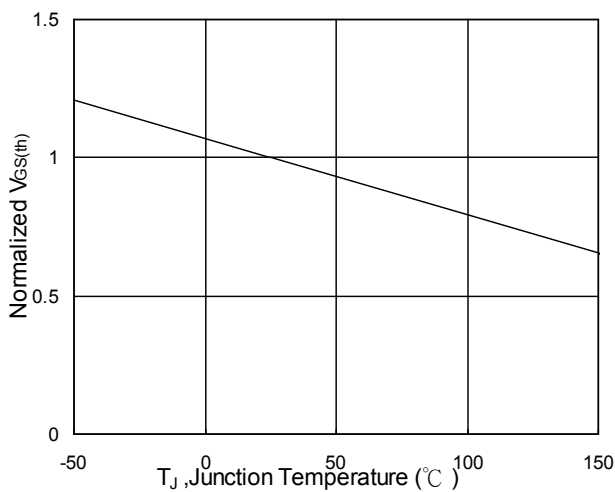


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

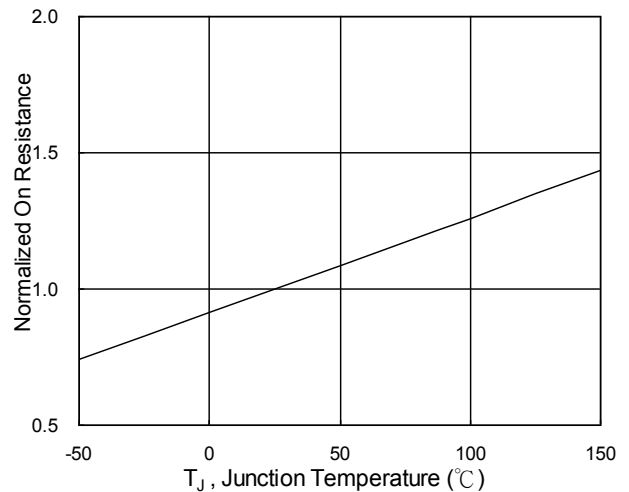


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

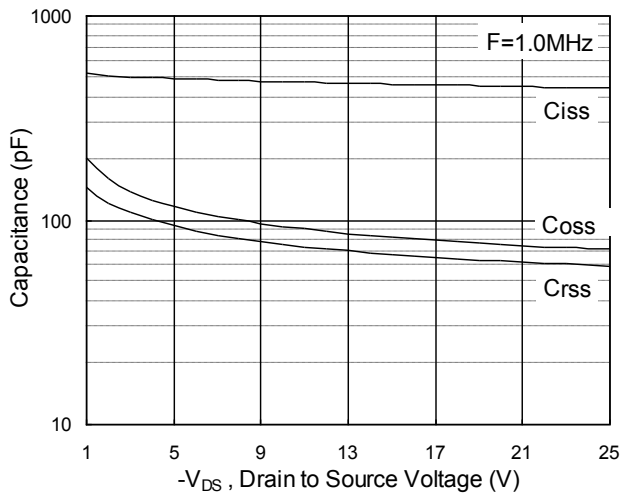


Fig.7 Capacitance

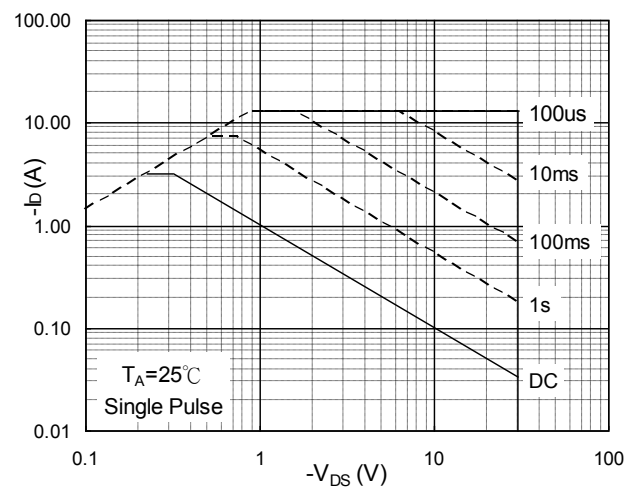


Fig.8 Safe Operating Area

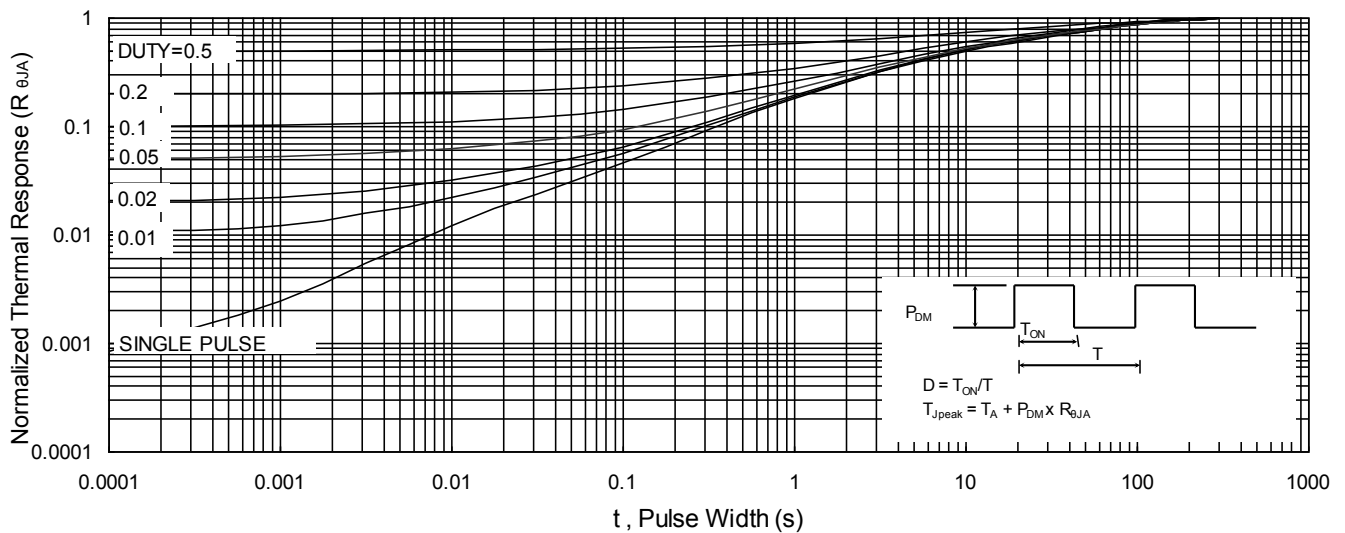


Fig.9 Normalized Maximum Transient Thermal Impedance

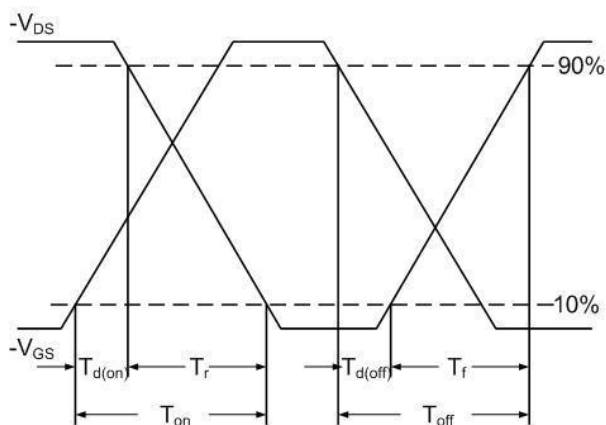


Fig.10 Switching Time Waveform

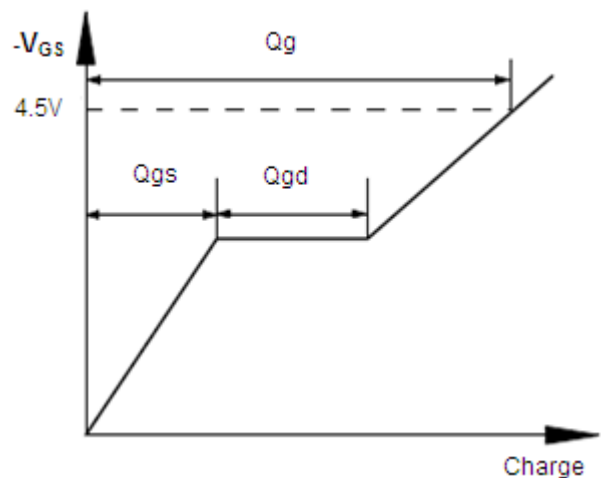
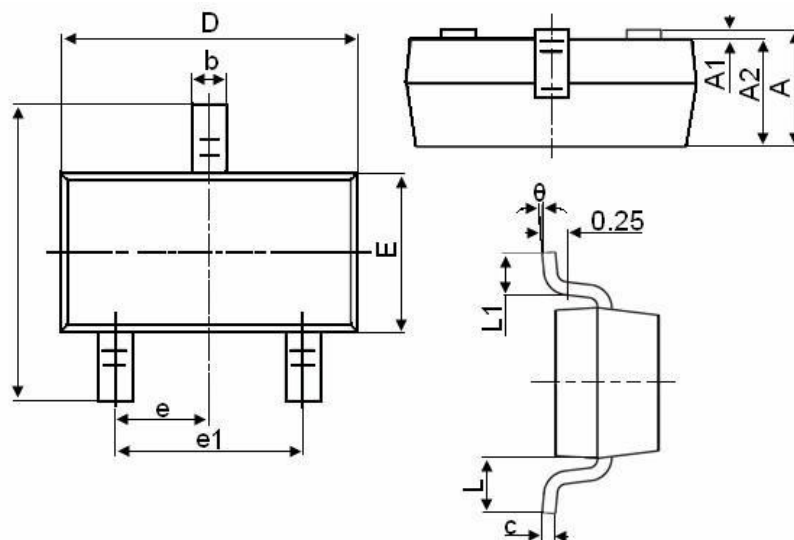


Fig.11 Gate Charge Waveform



SOT-23-3L(SOT-23F) Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
c	0.100	0.200
D	2.800	3.000
E	1.500	1.700
E1	2.650	2.950
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.600
θ	0°	8°



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